

Single Electron Transistor

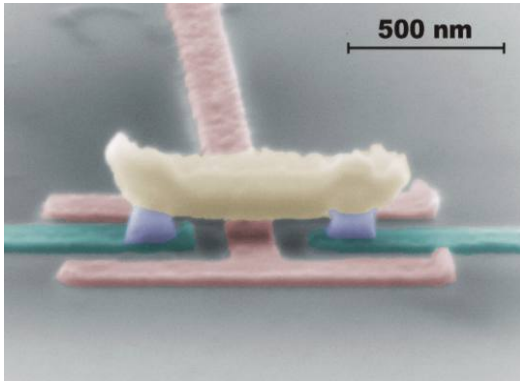
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Universität Regensburg

27. Juni 2006

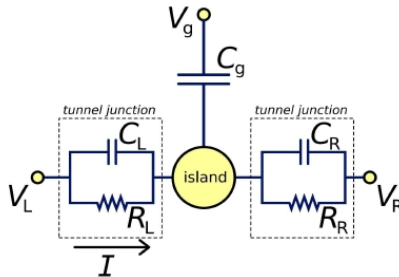
history

- ▶ 1985 conceptional proposal by Averin and Likharev
- ▶ 1987 realisation by Fulton und Dolan at Bell Labs



picture: Bell Labs, 1998

schematical view



picture: Norbert Nemec, 2005

condition for charge discretization

Which condition has to be fulfilled to observe discretization of charge?

► $E_c = \frac{e^2}{2C} \gg k_B T$

→ small size → small capacities → high energy

► example: sphere $C = 4\pi\epsilon_0 R$

► $R = \mu m \rightarrow T \cong 4 \text{ K}$

► $R = nm \rightarrow T \cong 300 \text{ K}$

calculation of charging energy:

- ▶ assumption: $V_l = -V_r$

$$\Rightarrow Q_0 = -eN_0 = C_l V_l + C_r V_r + C_g V_g = C_g V_g$$

- ▶ $\mu_l(N) = \frac{e^2(N-N_0)^2}{2C_{tot}}$ with $C_{tot} = C_l + C_r + C_g$

charging energy

► calculation:

$$\begin{aligned}\mu_I(N+1) - \mu_I(N) &= \frac{(e(N+1) + C_g V_g)^2}{2C_{tot}} - \frac{(eN + C_g V_g)^2}{2C_{tot}} = \\ &= \frac{e^2 N}{C_{tot}} + \frac{e^2}{2C_{tot}} + \frac{eC_g V_g}{C_{tot}}\end{aligned}$$

Energy Considerations (T=0): Tunneling from Source to Island (and vice versa)

Tunneling from Source to Island:

$$\blacktriangleright E_i = \sum_k^{\mu_s} \epsilon_k + \sum_k^{\mu_d} \epsilon_k + \mu_I(N)$$

$$\blacktriangleright E_f = \sum_k^{\mu_s} \epsilon_k - \epsilon_{\tilde{k}} + \sum_k^{\mu_d} \epsilon_k + \mu_I(N+1)$$

► Conservation of Energy:

$$E_i \stackrel{!}{=} E_f \quad \Rightarrow \quad \epsilon_{\tilde{k}} = \mu_I(N+1) - \mu_I(N) := \Delta\mu_I(N+1)$$

► tunneling:

$$\epsilon_{\tilde{k}} = \Delta\mu_I(N+1) \leq \mu_s = \frac{eV}{2}$$

Energy Considerations (T=0): Tunneling from Source to Island (and vice versa)

Tunneling from Island to Source:

- ▶ $E_i = \sum_k^{\mu_s} \epsilon_k + \sum_k^{\mu_d} \epsilon_k + \mu_I(N)$

- ▶ $E_f = \sum_k^{\mu_s} \epsilon_k + \epsilon_{\tilde{k}} + \sum_k^{\mu_d} \epsilon_k + \mu_I(N-1)$

- ▶ Conservation of Energy:

$$E_i \stackrel{!}{=} E_f \quad \Rightarrow \quad \epsilon_{\tilde{k}} = \mu_I(N) - \mu_I(N-1) := \Delta\mu_I(N)$$

- ▶ no tunneling:

$$\epsilon_{\tilde{k}} = \Delta\mu_I(N) < \mu_s = \frac{eV}{2}$$

Energy Considerations ($T=0$): Tunneling from Source to Island (and vice versa)

Coulomb Blockade:

- ▶ Voltage range in which Coulomb blockade effects (N is constant) can be observed:

$$\Delta\mu_I(N) < \frac{eV}{2} < \Delta\mu_I(N+1)$$

- ▶ For the voltage V one obtains:

$$\Delta\mu_I(N) \cdot \frac{2}{e} < V < \Delta\mu_I(N+1) \cdot \frac{2}{e}$$

- ▶ and respectively:

$$\frac{2C_g}{C_{tot}} V_g + \frac{2Ne}{C_{tot}} - \frac{e}{C_{tot}} < V < \frac{2C_g}{C_{tot}} V_g + \frac{2Ne}{C_{tot}} + \frac{e}{C_{tot}}$$

Energy Considerations (T=0): Tunneling from Island to Drain (and vice versa)

Tunneling from Island to Drain:

- ▶ $E_i = \sum_k^{\mu_s} \epsilon_k + \sum_k^{\mu_d} \epsilon_k + \mu_I(N)$

- ▶ $E_f = \sum_k^{\mu_s} \epsilon_k + \sum_k^{\mu_d} \epsilon_k + \epsilon_{\tilde{k}} + \mu_I(N-1)$

- ▶ Conservation of Energy:

$$E_i \stackrel{!}{=} E_f \quad \Rightarrow \quad \epsilon_{\tilde{k}} = \mu_I(N) - \mu_I(N-1) := \Delta\mu_I(N)$$

- ▶ no tunneling:

$$\epsilon_{\tilde{k}} = \Delta\mu_I(N+1) < \mu_d = -\frac{eV}{2}$$

Energy Considerations (T=0): Tunneling from Island to Drain (and vice versa)

Tunneling from Drain to Island:

$$\blacktriangleright E_i = \sum_k^{\mu_s} \epsilon_k + \sum_k^{\mu_d} \epsilon_k + \mu_I(N)$$

$$\blacktriangleright E_f = \sum_k^{\mu_s} \epsilon_k + \sum_k^{\mu_d} \epsilon_k - \epsilon_{\tilde{k}} + \mu_I(N+1)$$

► Conservation of Energy:

$$E_i \stackrel{!}{=} E_f \quad \Rightarrow \quad \epsilon_{\tilde{k}} = \mu_I(N+1) - \mu_I(N) := \Delta\mu_I(N+1)$$

► tunneling:

$$\epsilon_{\tilde{k}} = \Delta\mu_I(N+1) \leq \mu_d = -\frac{eV}{2}$$

Energy Considerations ($T=0$): Tunneling from Island to Drain (and vice versa)

Coulomb Blockade:

- ▶ Voltage range in which Coulomb blockade effects (N is constant) can be observed:

$$\Delta\mu_I(N) < -\frac{eV}{2} < \Delta\mu_I(N+1)$$

- ▶ For the voltage V one obtains:

$$-\Delta\mu_I(N+1) \cdot \frac{2}{e} < V < -\Delta\mu_I(N) \cdot \frac{2}{e}$$

- ▶ and respectively:

$$-\frac{2C_g}{C_{tot}} V_g - \frac{2Ne}{C_{tot}} - \frac{e}{C_{tot}} < V < -\frac{2C_g}{C_{tot}} V_g - \frac{2Ne}{C_{tot}} + \frac{e}{C_{tot}}$$

Energy Considerations ($T=0$): Overview

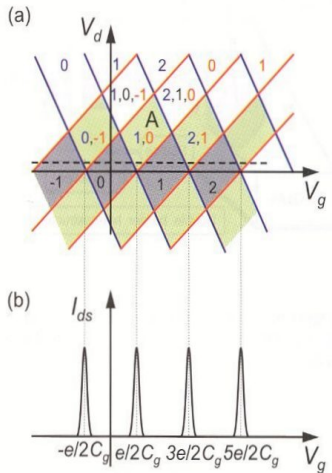
Conditions to observe Coulomb blockade effects::

- ▶ From Source/Island:

$$\frac{2C_g}{C_{tot}} V_g + \frac{2Ne}{C_{tot}} - \frac{e}{C_{tot}} < V < \frac{2C_g}{C_{tot}} V_g + \frac{2Ne}{C_{tot}} + \frac{e}{C_{tot}}$$

- ▶ From Island/Drain:

$$-\frac{2C_g}{C_{tot}} V_g - \frac{2Ne}{C_{tot}} - \frac{e}{C_{tot}} < V < -\frac{2C_g}{C_{tot}} V_g - \frac{2Ne}{C_{tot}} + \frac{e}{C_{tot}}$$



picture: Applied Physics, 1999

Numerical results

What we did:

- ▶ SET-routine with matlab
- ▶ playing with parameters
- ▶ try to explain results by theory

1. standard conditions

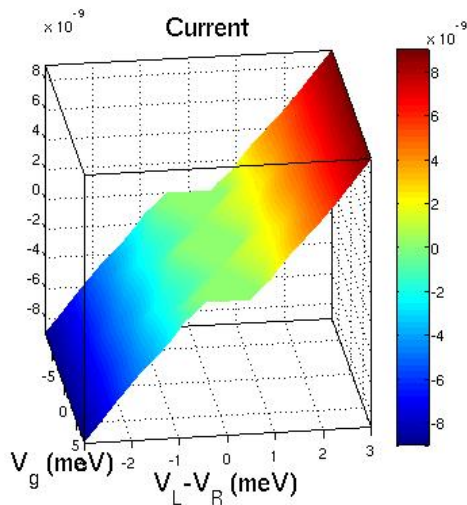
$$R_l = R_r$$

$$C_l = C_r$$

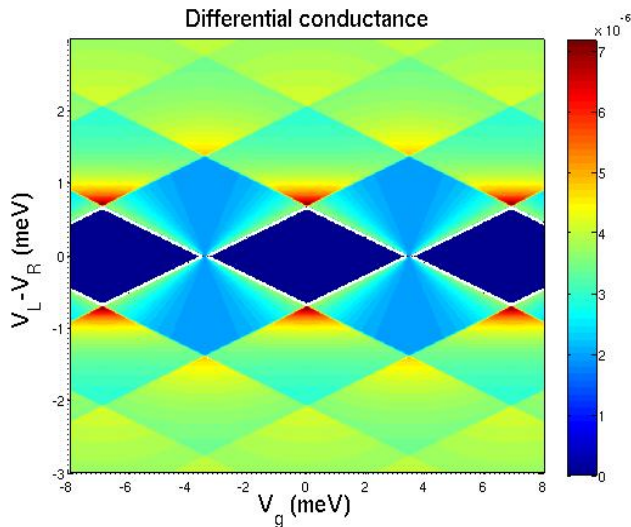
$$C_g \approx 1/4 \cdot C_{l/r}$$

$$T = 20mK$$

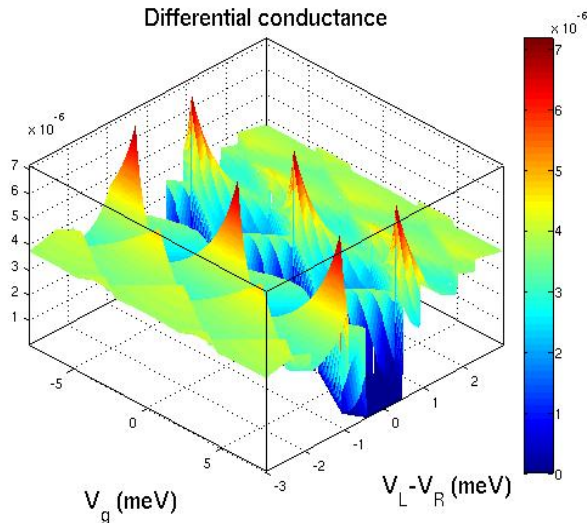
Resulting current



Differential conductance

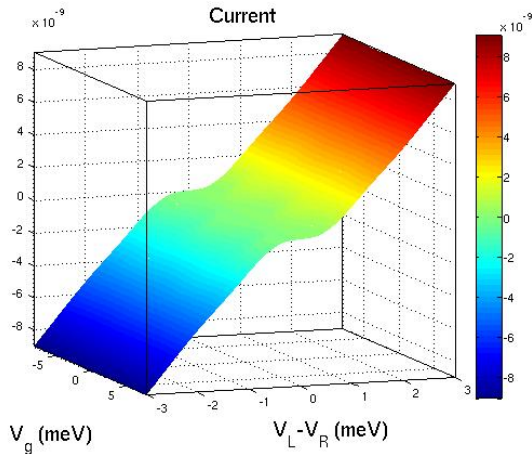


Differential conductance

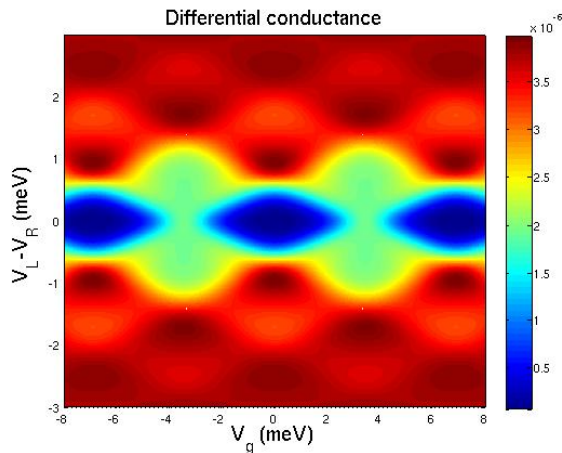


2. standard conditions, consideration of temperature dependency

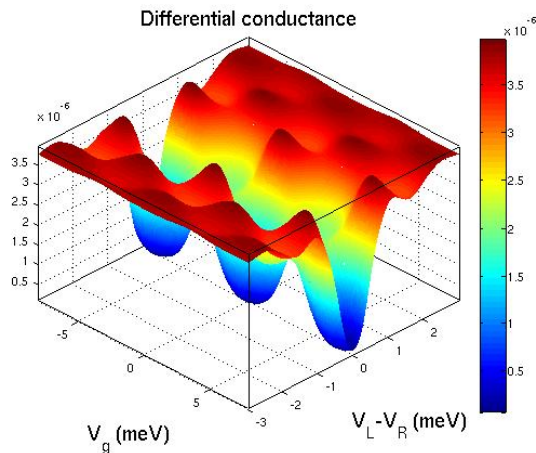
Resulting current at $T = 0.6K$



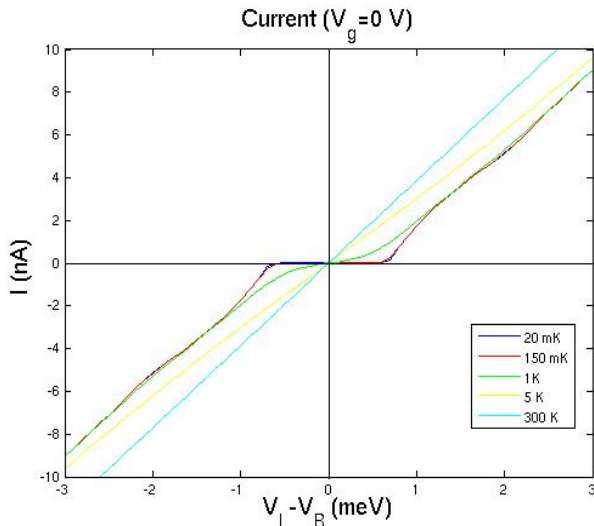
Differential conductance at $T = 0.6K$



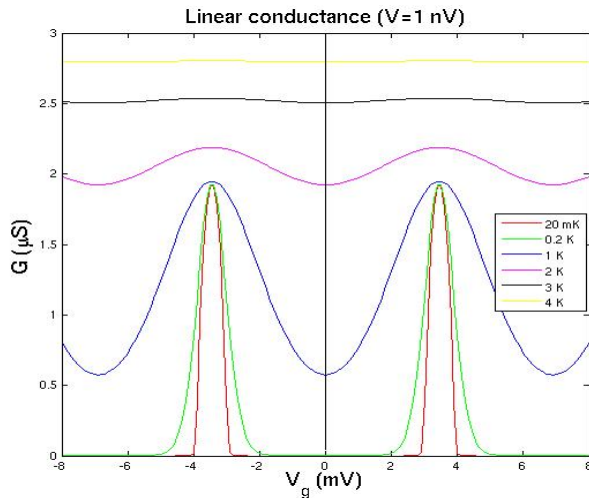
Differential conductance at $T = 0.6K$



Current vs. bias at different temperatures



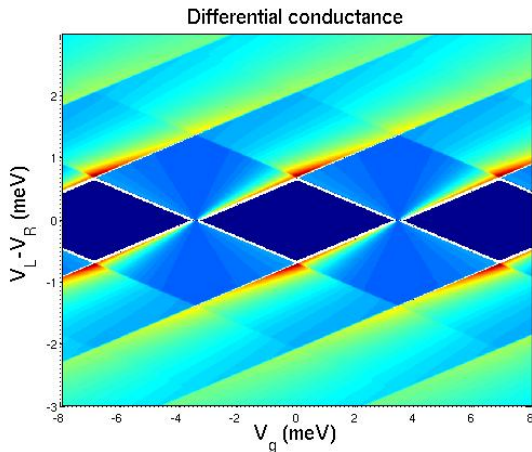
Coulomb oscillations



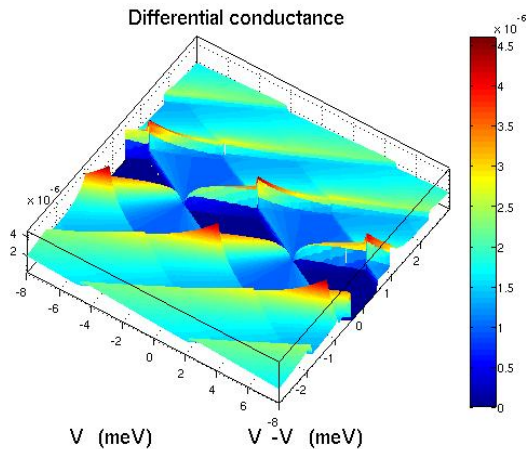
3. different proportions of resistances

$$\begin{aligned}C_l &= C_r \\C_g &\approx 1/4 \cdot C_{l/r} \\T &= 20mK\end{aligned}$$

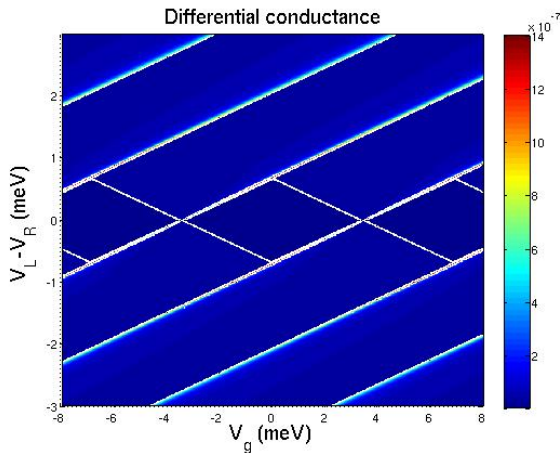
Differential conductance at $R_l = 3 \cdot R_r$



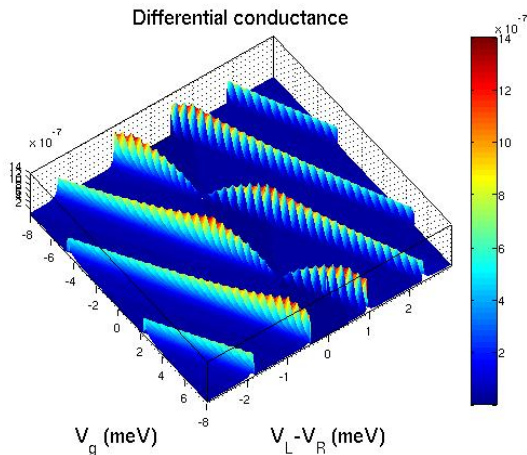
Differential conductance at $R_l = 3 \cdot R_r$



Differential conductance at $R_l = 1000 \cdot R_r$



Differential conductance at $R_l = 1000 \cdot R_r$

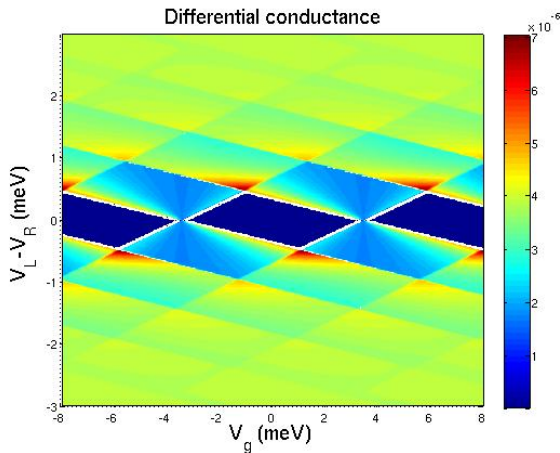


4. different proportions of capacities

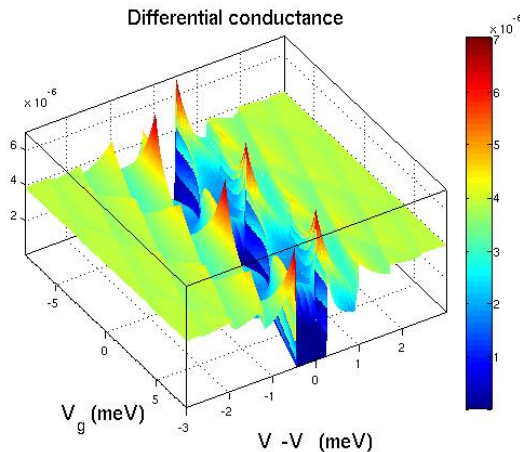
$$R_l = R_r$$

$$T = 20mK$$

Differential conductance at $C_l = 2 \cdot C_r$



Differential conductance at $C_l = 2 \cdot C_r$



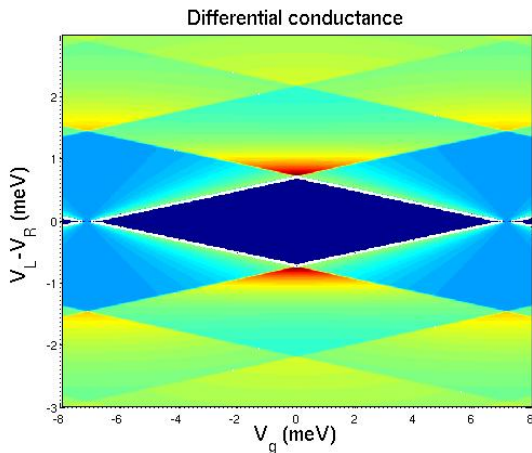
5. Altering the gate-capacity

$$C_l = C_r$$

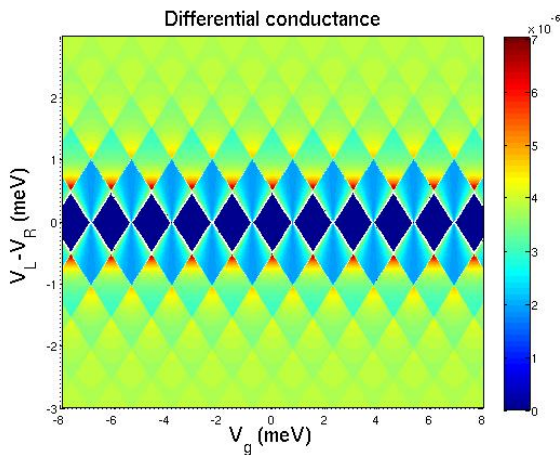
$$R_l = R_r$$

$$T = 20mK$$

Differential conductance at $C_g = 1/2 \cdot C_{g(\text{standard})}$



Differential conductance at $C_g \gg C_{g(\text{standard})}$



What's the gain of this worksheet?

- ▶ short insight to numerical physics
- ▶ first step for further studies in quantum electronics
- ▶ interesting results despite a low level of theory